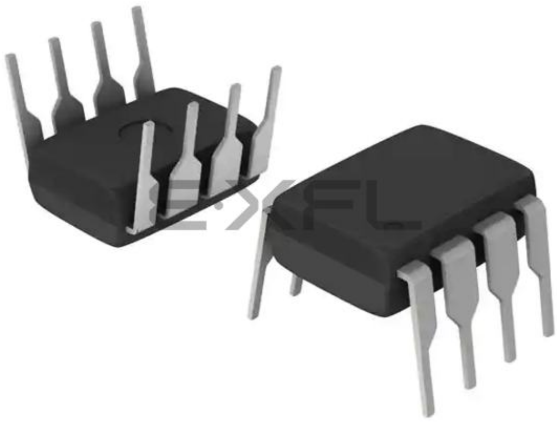

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	HC08
Core Size	8-Bit
Speed	8MHz
Connectivity	-
Peripherals	LVD, POR, PWM
Number of I/O	5
Program Memory Size	1.5KB (1.5K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128 x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 4x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Through Hole
Package / Case	8-DIP (0.300", 7.62mm)
Supplier Device Package	8-PDIP
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc68hc908qt2vpe

2.6 FLASH Memory (FLASH)

This subsection describes the operation of the embedded FLASH memory. The FLASH memory can be read, programmed, and erased from a single external supply. The program and erase operations are enabled through the use of an internal charge pump.

The FLASH memory consists of an array of 4096 or 1536 bytes with an additional 48 bytes for user vectors. The minimum size of FLASH memory that can be erased is 64 bytes; and the maximum size of FLASH memory that can be programmed in a program cycle is 32 bytes (a row). Program and erase operations are facilitated through control bits in the FLASH control register (FLCR). Details for these operations appear later in this section. The address ranges for the user memory and vectors are:

- $EE00 – $FDFF; user memory, 4096 bytes: MC68HC908QY4 and MC68HC908QT4
- $F800 – $FDFF; user memory, 1536 bytes: MC68HC908QY2, MC68HC908QT2, MC68HC908QY1 and MC68HC908QT1
- $FFD0 – $FFFF; user interrupt vectors, 48 bytes.

NOTE

An erased bit reads as a 1 and a programmed bit reads as a 0.
A security feature prevents viewing of the FLASH contents.(1)

2.6.1 FLASH Control Register

The FLASH control register (FLCR) controls FLASH program and erase operations.

Address: $FE08

	Bit 7	6	5	4	3	2	1	Bit 0
Read:	0	0	0	0	HVEN	MASS	ERASE	PGM
Write:								
Reset:	0	0	0	0	0	0	0	0

= Unimplemented

Figure 2-3. FLASH Control Register (FLCR)

HVEN — High Voltage Enable Bit

This read/write bit enables high voltage from the charge pump to the memory for either program or erase operation. It can only be set if either PGM =1 or ERASE =1 and the proper sequence for program or erase is followed.

1 = High voltage enabled to array and charge pump on
0 = High voltage disabled to array and charge pump off

MASS — Mass Erase Control Bit

This read/write bit configures the memory for mass erase operation.

1 = Mass erase operation selected
0 = Mass erase operation unselected

1. No security feature is absolutely secure. However, Freescale's strategy is to make reading or copying the FLASH difficult for unauthorized users.

8. Wait for time, t_{PROG} (minimum 30 μs).
9. Repeat step 7 and 8 until all desired bytes within the row are programmed.
10. Clear the PGM bit[1].
11. Wait for time, t_{NVH} (minimum 5 μs).
12. Clear the HVEN bit.
13. After time, t_{RCV} (typical 1 μs), the memory can be accessed in read mode again.

NOTE

The COP register at location $FFFF should not be written between steps 5–12, when the HVEN bit is set. Since this register is located at a valid FLASH address, unpredictable behavior may occur if this location is written while HVEN is set.

This program sequence is repeated throughout the memory until all data is programmed.

NOTE

Programming and erasing of FLASH locations cannot be performed by code being executed from the FLASH memory. While these operations must be performed in the order shown, other unrelated operations may occur between the steps. Do not exceed t_{PROG} maximum, see 16.16 Memory Characteristics.

2.6.5 FLASH Protection

Due to the ability of the on-board charge pump to erase and program the FLASH memory in the target application, provision is made to protect blocks of memory from unintentional erase or program operations due to system malfunction. This protection is done by use of a FLASH block protect register (FLBPR). The FLBPR determines the range of the FLASH memory which is to be protected. The range of the protected area starts from a location defined by FLBPR and ends to the bottom of the FLASH memory ($FFFF). When the memory is protected, the HVEN bit cannot be set in either ERASE or PROGRAM operations.

NOTE

In performing a program or erase operation, the FLASH block protect register must be read after setting the PGM or ERASE bit and before asserting the HVEN bit.

When the FLBPR is programmed with all 0 s, the entire memory is protected from being programmed and erased. When all the bits are erased (all 1's), the entire memory is accessible for program and erase.

When bits within the FLBPR are programmed, they lock a block of memory. The address ranges are shown in 2.6.6 FLASH Block Protect Register. Once the FLBPR is programmed with a value other than $FF, any erase or program of the FLBPR or the protected block of FLASH memory is prohibited. Mass erase is disabled whenever any block is protected (FLBPR does not equal $FF). The FLBPR itself can be erased or programmed only with an external voltage, V_{TST}, present on the $\overline{IRQ}$ pin. This voltage also allows entry from reset into the monitor mode.

2. The time between each FLASH address change, or the time between the last FLASH address programmed to clearing PGM bit, must not exceed the maximum programming time, t_{PROG} maximum.

3.3.2 Voltage Conversion

When the input voltage to the ADC equals V_{DD}, the ADC converts the signal to $FF (full scale). If the input voltage equals V_{SS}, the ADC converts it to $00. Input voltages between V_{DD} and V_{SS} are a straight-line linear conversion. All other input voltages will result in $FF if greater than V_{DD} and $00 if less than V_{SS}.

NOTE

Input voltage should not exceed the analog supply voltages.

3.3.3 Conversion Time

Sixteen ADC internal clocks are required to perform one conversion. The ADC starts a conversion on the first rising edge of the ADC internal clock immediately following a write to the ADSCR. If the ADC internal clock is selected to run at 1 MHz, then one conversion will take 16 μs to complete. With a 1-MHz ADC internal clock the maximum sample rate is 62.5 kHz.

$$\text{Conversion Time} = \frac{\text{16 ADC Clock Cycles}}{\text{ADC Clock Frequency}}$$

$$\text{Number of Bus Cycles} = \text{Conversion Time} \times \text{Bus Frequency}$$

3.3.4 Continuous Conversion

In the continuous conversion mode (ADCO = 1), the ADC continuously converts the selected channel filling the ADC data register (ADR) with new data after each conversion. Data from the previous conversion will be overwritten whether that data has been read or not. Conversions will continue until the ADCO bit is cleared. The COCO bit (ADSCR, $003C) is set after each conversion and will stay set until the next read of the ADC data register.

When a conversion is in process and the ADSCR is written, the current conversion data should be discarded to prevent an incorrect reading.

3.3.5 Accuracy and Precision

The conversion process is monotonic and has no missing codes.

3.4 Interrupts

When the AIEN bit is set, the ADC module is capable of generating a central processor unit (CPU) interrupt after each ADC conversion. A CPU interrupt is generated if the COCO bit is at 0. The COCO bit is not used as a conversion complete flag when interrupts are enabled.

3.5 Low-Power Modes

The following subsections describe the ADC in low-power modes.

3.5.1 Wait Mode

The ADC continues normal operation during wait mode. Any enabled CPU interrupt request from the ADC can bring the microcontroller unit (MCU) out of wait mode. If the ADC is not required to bring the MCU out of wait mode, power down the ADC by setting the CH[4:0] bits in ADSCR to 1s before executing the WAIT instruction.

Table 7-1. Instruction Set Summary (Sheet 3 of 6)

Source Form	Operation	Description	Effect on CCR						Address Mode	Opcode	Operand	Cycles
			V	H	I	N	Z	C				
CLI	Clear Interrupt Mask	I ← 0	–	–	0	–	–	–	INH	9A		2
CLR *opr* CLRA CLRX CLRH CLR *opr*,X CLR ,X CLR *opr*,SP	Clear	M ← \$00 A ← \$00 X ← \$00 H ← \$00 M ← \$00 M ← \$00 M ← \$00	0	–	–	0	1	–	DIR INH INH INH IX1 IX SP1	3F 4F 5F 8C 6F 7F 9E6F	dd ff ff	3 1 1 1 3 2 4
CMP #*opr* CMP *opr* CMP *opr* CMP *opr*,X CMP *opr*,X CMP ,X CMP *opr*,SP CMP *opr*,SP	Compare A with M	(A) – (M)	↕	–	–	↕	↕	↕	IMM DIR EXT IX2 IX1 IX SP1 SP2	A1 B1 C1 D1 E1 F1 9EE1 9ED1	ii dd hh ll ee ff ff ff ee ff	2 3 4 4 3 2 4 5
COM *opr* COMA COMX COM *opr*,X COM ,X COM *opr*,SP	Complement (One's Complement)	M ← $(\overline{M})$ = \$FF – (M) A ← $(\overline{A})$ = \$FF – (M) X ← $(\overline{X})$ = \$FF – (M) M ← $(\overline{M})$ = \$FF – (M) M ← $(\overline{M})$ = \$FF – (M) M ← $(\overline{M})$ = \$FF – (M)	0	–	–	↕	↕	1	DIR INH INH IX1 IX SP1	33 43 53 63 73 9E63	dd ff ff	4 1 1 4 3 5
CPHX #*opr* CPHX *opr*	Compare H:X with M	(H:X) – (M:M + 1)	↕	–	–	↕	↕	↕	IMM DIR	65 75	ii ii+1 dd	3 4
CPX #*opr* CPX *opr* CPX *opr* CPX ,X CPX *opr*,X CPX *opr*,X CPX *opr*,SP CPX *opr*,SP	Compare X with M	(X) – (M)	↕	–	–	↕	↕	↕	IMM DIR EXT IX2 IX1 IX SP1 SP2	A3 B3 C3 D3 E3 F3 9EE3 9ED3	ii dd hh ll ee ff ff ff ee ff	2 3 4 4 3 2 4 5
DAA	Decimal Adjust A	$(A)_{10}$	U	–	–	↕	↕	↕	INH	72		2
DBNZ *opr,rel* DBNZA *rel* DBNZX *rel* DBNZ *opr*,X,*rel* DBNZ X,*rel* DBNZ *opr*,SP,*rel*	Decrement and Branch if Not Zero	A ← (A) – 1 or M ← (M) – 1 or X ← (X) – 1 PC ← (PC) + 3 + *rel* ? (result) ≠ 0 PC ← (PC) + 2 + *rel* ? (result) ≠ 0 PC ← (PC) + 2 + *rel* ? (result) ≠ 0 PC ← (PC) + 3 + *rel* ? (result) ≠ 0 PC ← (PC) + 2 + *rel* ? (result) ≠ 0 PC ← (PC) + 4 + *rel* ? (result) ≠ 0	–	–	–	–	–	–	DIR INH INH IX1 IX SP1	3B 4B 5B 6B 7B 9E6B	dd rr rr rr ff rr rr ff rr	5 3 3 5 4 6
DEC *opr* DECA DECX DEC *opr*,X DEC ,X DEC *opr*,SP	Decrement	M ← (M) – 1 A ← (A) – 1 X ← (X) – 1 M ← (M) – 1 M ← (M) – 1 M ← (M) – 1	↕	–	–	↕	↕	–	DIR INH INH IX1 IX SP1	3A 4A 5A 6A 7A 9E6A	dd ff ff	4 1 1 4 3 5
DIV	Divide	A ← (H:A)/(X) H ← Remainder	–	–	–	–	↕	↕	INH	52		7
EOR #*opr* EOR *opr* EOR *opr* EOR *opr*,X EOR *opr*,X EOR ,X EOR *opr*,SP EOR *opr*,SP	Exclusive OR M with A	A ← (A ⊕ M)	0	–	–	↕	↕	–	IMM DIR EXT IX2 IX1 IX SP1 SP2	A8 B8 C8 D8 E8 F8 9EE8 9ED8	ii dd hh ll ee ff ff ff ee ff	2 3 4 4 3 2 4 5
INC *opr* INCA INCX INC *opr*,X INC ,X INC *opr*,SP	Increment	M ← (M) + 1 A ← (A) + 1 X ← (X) + 1 M ← (M) + 1 M ← (M) + 1 M ← (M) + 1	↕	–	–	↕	↕	–	DIR INH INH IX1 IX SP1	3C 4C 5C 6C 7C 9E6C	dd ff ff	4 1 1 4 3 5

V_{TRIPF}. Setting the LVI enable in stop mode bit, LVISTOP, enables the LVI to operate in stop mode. Setting the LVI 5-V or 3-V trip point bit, LVI5OR3, enables the trip point voltage, V_{TRIPF}, to be configured for 5-V operation. Clearing the LVI5OR3 bit enables the trip point voltage, V_{TRIPF}, to be configured for 3-V operation. The actual trip thresholds are specified in 16.5 5-V DC Electrical Characteristics and 16.9 3-V DC Electrical Characteristics.

NOTE

After a power-on reset, the LVI's default mode of operation is 3 volts. If a 5-V system is used, the user must set the LVI5OR3 bit to raise the trip point to 5-V operation.

If the user requires 5-V mode and sets the LVI5OR3 bit after power-on reset while the V_{DD} supply is not above the V_{TRIPR} for 5-V mode, the microcontroller unit (MCU) will immediately go into reset. The next time the LVI releases the reset, the supply will be above the V_{TRIPR} for 5-V mode.

Once an LVI reset occurs, the MCU remains in reset until V_{DD} rises above a voltage, V_{TRIPR}, which causes the MCU to exit reset. See Chapter 13 System Integration Module (SIM) for the reset recovery sequence.

The output of the comparator controls the state of the LVIOUT flag in the LVI status register (LVISR) and can be used for polling LVI operation when the LVI reset is disabled.

10.3.1 Polled LVI Operation

In applications that can operate at V_{DD} levels below the V_{TRIPF} level, software can monitor V_{DD} by polling the LVIOUT bit. In the configuration register, the LVIPWRD bit must be cleared to enable the LVI module, and the LVIRSTD bit must be at set to disable LVI resets.

10.3.2 Forced Reset Operation

In applications that require V_{DD} to remain above the V_{TRIPF} level, enabling LVI resets allows the LVI module to reset the MCU when V_{DD} falls below the V_{TRIPF} level. In the configuration register, the LVIPWRD and LVIRSTD bits must be cleared to enable the LVI module and to enable LVI resets.

10.3.3 Voltage Hysteresis Protection

Once the LVI has triggered (by having V_{DD} fall below V_{TRIPF}), the LVI will maintain a reset condition until V_{DD} rises above the rising trip point voltage, V_{TRIPR}. This prevents a condition in which the MCU is continually entering and exiting reset if V_{DD} is approximately equal to V_{TRIPF}. V_{TRIPR} is greater than V_{TRIPF} by the hysteresis voltage, V_{HYS}.

10.3.4 LVI Trip Selection

The LVI5OR3 bit in the configuration register selects whether the LVI is configured for 5-V or 3-V protection.

NOTE

The microcontroller is guaranteed to operate at a minimum supply voltage. The trip point (V_{TRIPF} [5 V] or V_{TRIPF} [3 V]) may be lower than this. See 16.5 5-V DC Electrical Characteristics and 16.9 3-V DC Electrical Characteristics for the actual trip point voltages.

10.4 LVI Status Register

The LVI status register (LVISR) indicates if the V_{DD} voltage was detected below the V_{TRIPF} level while LVI resets have been disabled.

Address: $FE0C

	Bit 7	6	5	4	3	2	1	Bit 0
Read:	LVIOUT	0	0	0	0	0	0	R
Write:								
Reset:	0	0	0	0	0	0	0	0

= Unimplemented   R = Reserved

Figure 10-2. LVI Status Register (LVISR)

LVIOUT — LVI Output Bit

This read-only flag becomes set when the V_{DD} voltage falls below the V_{TRIPF} trip voltage and is cleared when V_{DD} voltage rises above V_{TRIPR}. The difference in these threshold levels results in a hysteresis that prevents oscillation into and out of reset (see Table 10-1). Reset clears the LVIOUT bit.

Table 10-1. LVIOUT Bit Indication

V_{DD}	LVIOUT
$V_{DD} > V_{TRIPR}$	0
$V_{DD} < V_{TRIPF}$	1
$V_{TRIPF} < V_{DD} < V_{TRIPR}$	Previous value

10.5 LVI Interrupts

The LVI module does not generate interrupt requests.

10.6 Low-Power Modes

The STOP and WAIT instructions put the MCU in low power-consumption standby modes.

10.6.1 Wait Mode

If enabled, the LVI module remains active in wait mode. If enabled to generate resets, the LVI module can generate a reset and bring the MCU out of wait mode.

10.6.2 Stop Mode

When the LVIPWRD bit in the configuration register is cleared and the LVISTOP bit in the configuration register is set, the LVI module remains active in stop mode. If enabled to generate resets, the LVI module can generate a reset and bring the MCU out of stop mode.

11.8.1 Oscillator Status Register

The oscillator status register (OSCSTAT) contains the bits for switching from internal to external clock sources.

Address: $0036

	Bit 7	6	5	4	3	2	1	Bit 0
Read:	R	R	R	R	R	R	ECGON	ECGST
Write:								
Reset:	0	0	0	0	0	0	0	0

R = Reserved; (shaded) = Unimplemented

Figure 11-4. Oscillator Status Register (OSCSTAT)

ECGON — External Clock Generator On Bit

This read/write bit enables external clock generator, so that the switching process can be initiated. This bit is forced low during reset. This bit is ignored in monitor mode with the internal oscillator bypassed, PTM or CTM mode.

1 = External clock generator enabled
0 = External clock generator disabled

ECGST — External Clock Status Bit

This read-only bit indicates whether or not an external clock source is engaged to drive the system clock.

1 = An external clock source engaged
0 = An external clock source disengaged

11.8.2 Oscillator Trim Register (OSCTRIM)

Address: $0038

	Bit 7	6	5	4	3	2	1	Bit 0
Read:/Write:	TRIM7	TRIM6	TRIM5	TRIM4	TRIM3	TRIM2	TRIM1	TRIM0
Reset:	1	0	0	0	0	0	0	0

Figure 11-5. Oscillator Trim Register (OSCTRIM)

TRIM7–TRIM0 — Internal Oscillator Trim Factor Bits

These read/write bits change the size of the internal capacitor used by the internal oscillator. By measuring the period of the internal clock and adjusting this factor accordingly, the frequency of the internal clock can be fine tuned. Increasing (decreasing) this factor by one increases (decreases) the period by approximately 0.2% of the untrimmed period (the period for TRIM = $80). The trimmed frequency is guaranteed not to vary by more than ±5% over the full specified range of temperature and voltage. The reset value is $80, which sets the frequency to 12.8 MHz (3.2 MHz bus speed) ±25%.

Applications using the internal oscillator should copy the internal oscillator trim value at location $FFC0 or $FFC1 into this register to trim the clock source.

Figure 12-3 shows the port A I/O logic.

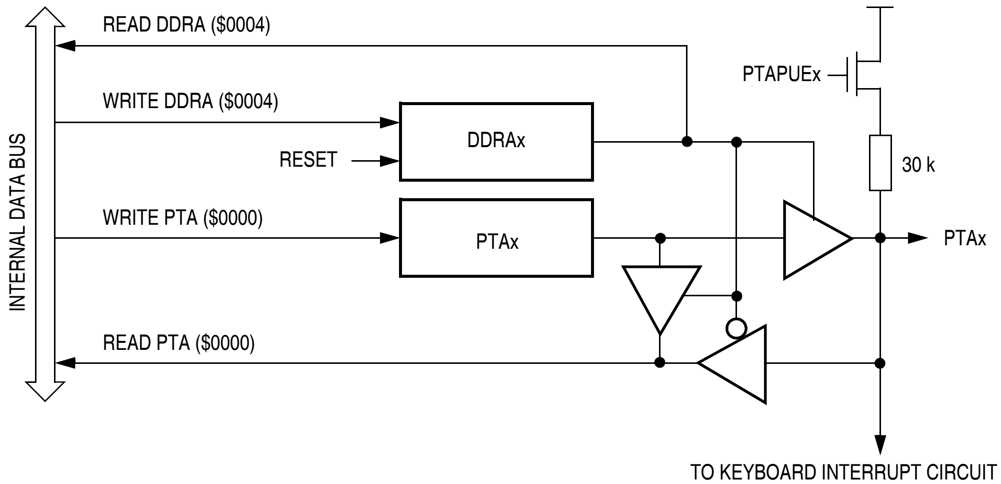


Figure 12-3. Port A I/O Circuit

NOTE

Figure 12-3 does not apply to PTA2

When DDRAx is a 1, reading address $0000 reads the PTAx data latch. When DDRAx is a 0, reading address $0000 reads the voltage level on the pin. The data latch can always be written, regardless of the state of its data direction bit.

12.2.3 Port A Input Pullup Enable Register

The port A input pullup enable register (PTAPUE) contains a software configurable pullup device for each if the six port A pins. Each bit is individually configurable and requires the corresponding data direction register, DDRAx, to be configured as input. Each pullup device is automatically and dynamically disabled when its corresponding DDRAx bit is configured as output.

Address: $000B

	Bit 7	6	5	4	3	2	1	Bit 0
Read: / Write:	OSC2EN		PTAPUE5	PTAPUE4	PTAPUE3	PTAPUE2	PTAPUE1	PTAPUE0
Reset:	0	0	0	0	0	0	0	0

= Unimplemented

Figure 12-4. Port A Input Pullup Enable Register (PTAPUE)

OSC2EN — Enable PTA4 on OSC2 Pin

This read/write bit configures the OSC2 pin function when internal oscillator or RC oscillator option is selected. This bit has no effect for the XTAL or external oscillator options.

1 = OSC2 pin outputs the internal or RC oscillator clock (BUSCLKX4)
0 = OSC2 pin configured for PTA4 I/O, having all the interrupt and pullup functions

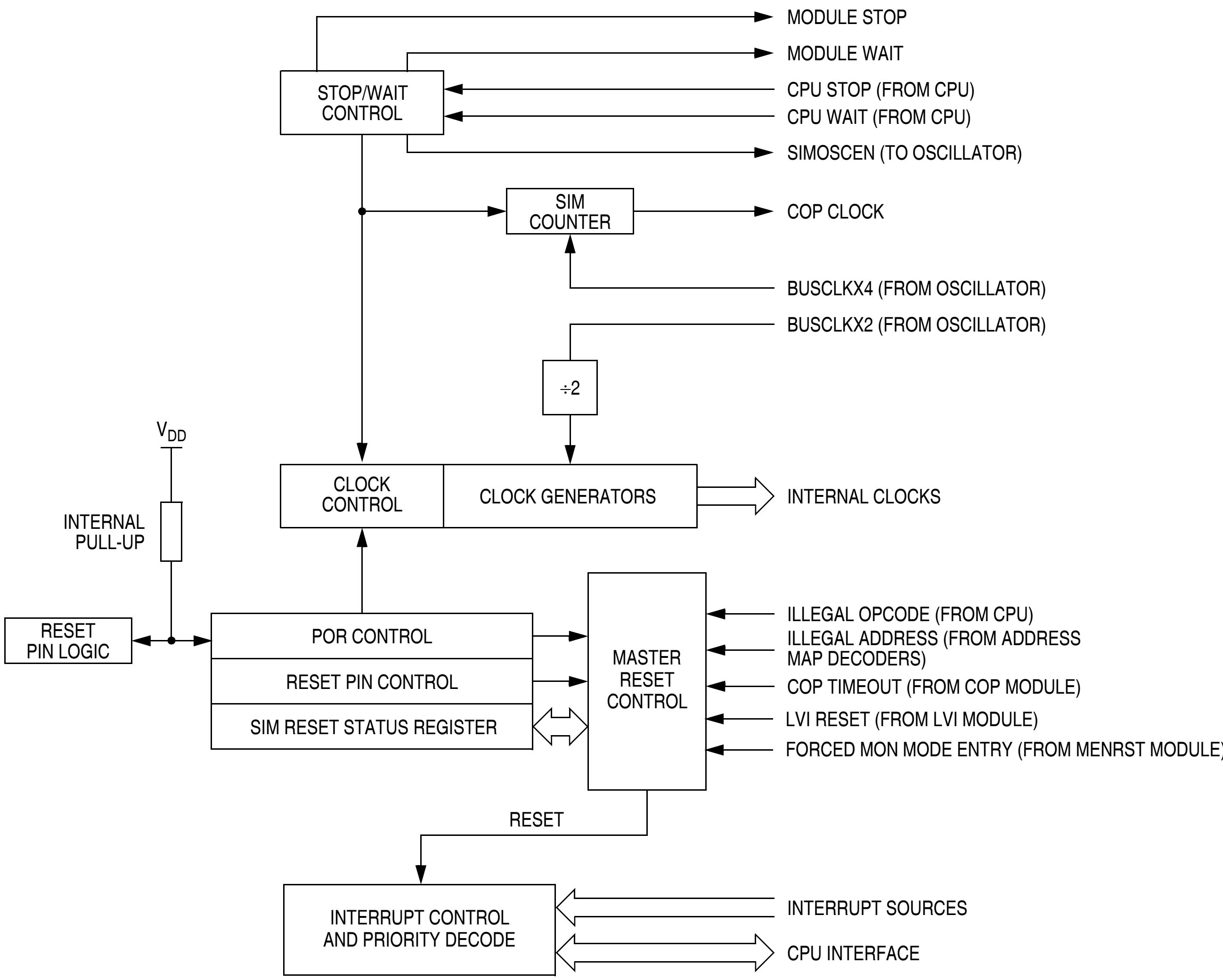


Figure 13-1. SIM Block Diagram

13.2 $\overline{\text{RST}}$ and $\overline{\text{IRQ}}$ Pins Initialization

$\overline{\text{RST}}$ and $\overline{\text{IRQ}}$ pins come out of reset as PTA3 and PTA2 respectively. $\overline{\text{RST}}$ and $\overline{\text{IRQ}}$ functions can be activated by programing CONFIG2 accordingly. Refer to Chapter 5 Configuration Register (CONFIG).

13.3 SIM Bus Clock Control and Generation

The bus clock generator provides system clock signals for the CPU and peripherals on the MCU. The system clocks are generated from an incoming clock, BUSCLKX2, as shown in Figure 13-2.

13.4.1 External Pin Reset

The $\overline{\text{RST}}$ pin circuits include an internal pullup device. Pulling the asynchronous $\overline{\text{RST}}$ pin low halts all processing. The PIN bit of the SIM reset status register (SRSR) is set as long as $\overline{\text{RST}}$ is held low for at least the minimum t_{RL} time. Figure 13-3 shows the relative timing. The $\overline{\text{RST}}$ pin function is only available if the RSTEN bit is set in the CONFIG2 register.

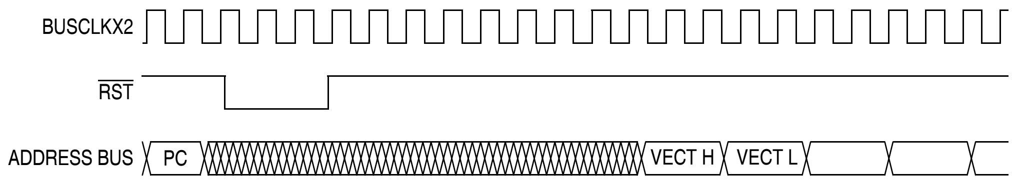


Figure 13-3. External Reset Timing

13.4.2 Active Resets from Internal Sources

The $\overline{\text{RST}}$ pin is initially setup as a general-purpose input after a POR. Setting the RSTEN bit in the CONFIG2 register enables the pin for the reset function. This section assumes the RSTEN bit is set when describing activity on the $\overline{\text{RST}}$ pin.

NOTE

For POR and LVI resets, the SIM cycles through 4096 BUSCLKX4 cycles during which the SIM forces the $\overline{\text{RST}}$ pin low. The internal reset signal then follows the sequence from the falling edge of $\overline{\text{RST}}$ shown in Figure 13-4.

The COP reset is asynchronous to the bus clock.

The active reset feature allows the part to issue a reset to peripherals and other chips within a system built around the MCU.

All internal reset sources actively pull the $\overline{\text{RST}}$ pin low for 32 BUSCLKX4 cycles to allow resetting of external peripherals. The internal reset signal IRST continues to be asserted for an additional 32 cycles (see Figure 13-4). An internal reset can be caused by an illegal address, illegal opcode, COP time out, LVI, or POR (see Figure 13-5).

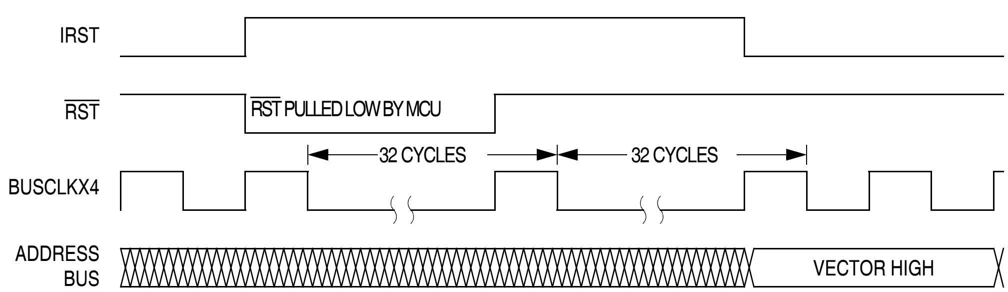


Figure 13-4. Internal Reset Timing

14.4 Functional Description

Figure 14-2 shows the structure of the TIM. The central component of the TIM is the 16-bit TIM counter that can operate as a free-running counter or a modulo up-counter. The TIM counter provides the timing reference for the input capture and output compare functions. The TIM counter modulo registers, TMODH:TMODL, control the modulo value of the TIM counter. Software can read the TIM counter value at any time without affecting the counting sequence.

The two TIM channels are programmable independently as input capture or output compare channels.

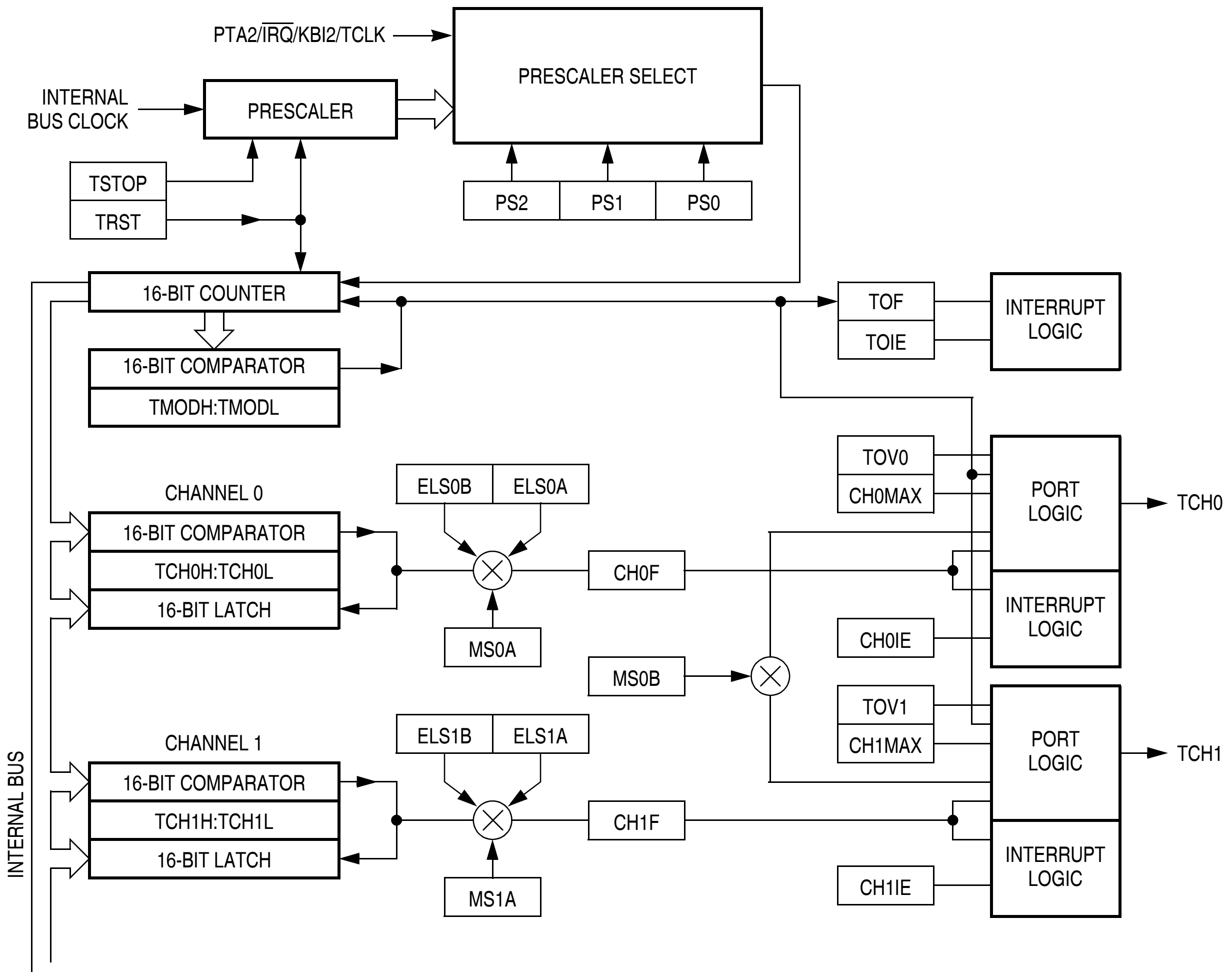


Figure 14-2. TIM Block Diagram

Table 15-2. Mode Difference

Modes	Functions					
	Reset Vector High	Reset Vector Low	Break Vector High	Break Vector Low	SWI Vector High	SWI Vector Low
User	$FFFE	$FFFF	$FFFC	$FFFD	$FFFC	$FFFD
Monitor	$FEFE	$FEFF	$FEFC	$FEFD	$FEFC	$FEFD

15.3.1.4 Data Format

Communication with the monitor ROM is in standard non-return-to-zero (NRZ) mark/space data format. Transmit and receive baud rates must be identical.

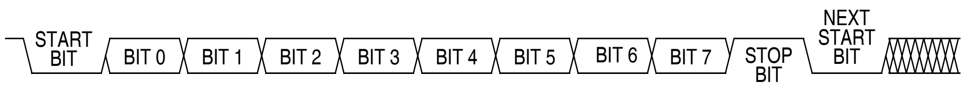


Figure 15-13. Monitor Data Format

15.3.1.5 Break Signal

A start bit (logic 0) followed by nine logic 0 bits is a break signal. When the monitor receives a break signal, it drives the PTA0 pin high for the duration of two bits and then echoes back the break signal.

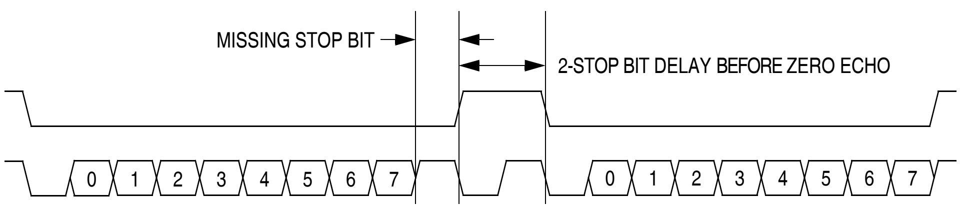


Figure 15-14. Break Transaction

15.3.1.6 Baud Rate

The monitor communication baud rate is controlled by the frequency of the external or internal oscillator and the state of the appropriate pins as shown in Table 15-1.

Table 15-1 also lists the bus frequencies to achieve standard baud rates. The effective baud rate is the bus frequency divided by 256 when using an external oscillator. When using the internal oscillator in forced monitor mode, the effective baud rate is the bus frequency divided by 335.

15.3.1.7 Commands

The monitor ROM firmware uses these commands:

- READ (read memory)
- WRITE (write memory)
- IREAD (indexed read)
- IWRITE (indexed write)
- READSP (read stack pointer)
- RUN (run user program)

16.11 3-V Control Timing

Characteristic[1]	Symbol	Min	Max	Unit
Internal operating frequency	f_{OP} (f_{Bus})	—	4	MHz
Internal clock period ($1/f_{OP}$)	t_{cyc}	250	—	ns
$\overline{\text{RST}}$ input pulse width low	t_{RL}	200	—	ns
$\overline{\text{IRQ}}$ interrupt pulse width low (edge-triggered)	t_{ILIH}	200	—	ns
$\overline{\text{IRQ}}$ interrupt pulse period	t_{ILIL}	Note[2]	—	t_{cyc}

1. V_{DD} = 2.7 to 3.3 Vdc, V_{SS} = 0 Vdc, $T_A = T_L$ to T_H; timing shown with respect to 20% V_{DD} and 70% V_{DD}, unless otherwise noted.
2. The minimum period is the number of cycles it takes to execute the interrupt service routine plus 1 t_{cyc}.

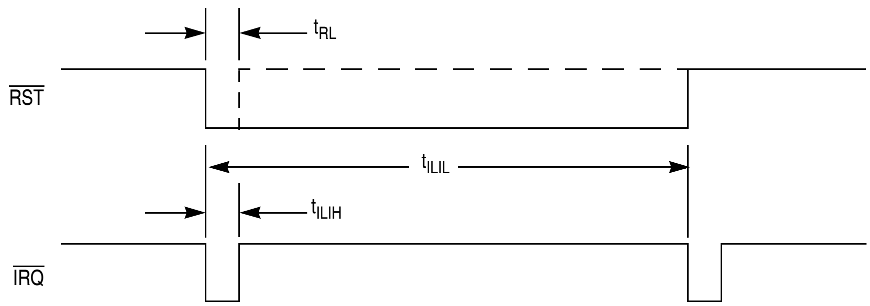


Figure 16-7. $\overline{\text{RST}}$ and $\overline{\text{IRQ}}$ Timing

16.13 Supply Current Characteristics

Characteristic[1]	Voltage	Bus Frequency (MHz)	Symbol	Typ[2]	Max	Unit
Run Mode V_{DD} supply current[3]	5.0 3.0	3.2 3.2	RI_{DD}	6.0 2.5	7.0 3.2	mA
Wait Mode V_{DD} supply current[4]	5.0 3.0	3.2 3.2	WI_{DD}	1.0 0.67	1.5 1.0	mA mA
Stop Mode V_{DD} supply current[5] –40 to 85•C –40 to 105•C –40 to 125•C 25•C with auto wakeup enabled Incremental current with LVI enabled at 25•C	5.0		SI_{DD}	0.04 — — 7 125	1.0 2.0 5.0 — —	µA
Stop Mode V_{DD} supply current[5] –40 to 85•C –40 to 105•C –40 to 125•C 25•C with auto wakeup enabled Incremental current with LVI enabled at 25•C	3.0		SI_{DD}	0.02 — — 5 100	0.5 1.0 4.0 — —	µA

1. V_{SS} = 0 Vdc, $T_A = T_L$ to T_H, unless otherwise noted.
2. Typical values reflect average measurements at 25•C only.
3. Run (operating) I_{DD} measured using trimmed internal oscillator, ADC off, all other modules enabled. All pins configured as inputs and tied to 0.2 V from rail.
4. Wait I_{DD} measured using trimmed internal oscillator, ADC off, all other modules enabled. All pins configured as inputs and tied to 0.2 V from rail.
5. Stop I_{DD} measured with all pins tied to 0.2 V or less from rail. No dc loads. On the 8-pin versions, port B is configured as inputs with pullups enabled.

16.16 Memory Characteristics

Characteristic	Symbol	Min	Typ	Max	Unit
RAM data retention voltage	V_{RDR}	1.3	—	—	V
FLASH program bus clock frequency	—	1	—	—	MHz
FLASH read bus clock frequency	f_{Read}[(1)]	0	—	8 M	Hz
FLASH page erase time <1 k cycles >1 k cycles	t_{Erase}	 0.9 3.6	 1 4	 1.1 5.5	ms
FLASH mass erase time	t_{MErase}	4	—	—	ms
FLASH PGM/ERASE to HVEN setup time	t_{NVS}	10	—	—	μs
FLASH high-voltage hold time	t_{NVH}	5	—	—	μs
FLASH high-voltage hold time (mass erase)	t_{NVHL}	100	—	—	μs
FLASH program hold time	t_{PGS}	5	—	—	μs
FLASH program time	t_{PROG}	30	—	40	μs
FLASH return to read time	t_{RCV}[(2)]	1	—	—	μs
FLASH cumulative program HV period	t_{HV}[(3)]	—	—	4	ms
FLASH endurance[(4)]	—	10 k	100 k	—	Cycles
FLASH data retention time[(5)]	—	15	100	—	Years

1. f_{Read} is defined as the frequency range for which the FLASH memory can be read.
2. t_{RCV} is defined as the time it needs before the FLASH can be read after turning off the high voltage charge pump, by clearing HVEN to 0.
3. t_{HV} is defined as the cumulative high voltage programming time to the same row before next erase.
   t_{HV} must satisfy this condition: $t_{NVS} + t_{NVH} + t_{PGS} + (t_{PROG} \times 32) \leq t_{HV}$ maximum.
4. Typical endurance was evaluated for this product family. For additional information on how Freescale defines *Typical Endurance*, please refer to Engineering Bulletin EB619.
5. Typical data retention values are based on intrinsic capability of the technology measured at high temperature and de-rated to 25•C using the Arrhenius equation. For additional information on how Freescale defines *Typical Data Retention*, please refer to Engineering Bulletin EB618.

NOTES:

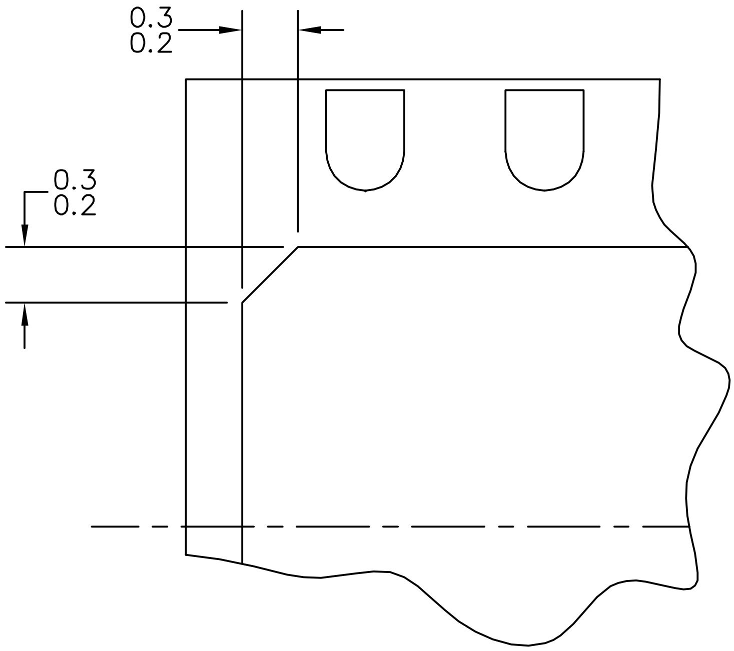
1. DIMENSIONS AND TOLERANCES PER ASME Y14.5–1994.

2. CONTROLLING DIMENSION: MILLIMETER.

3. DIMENSIONS DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEDD 0.15mm PER SIDE.

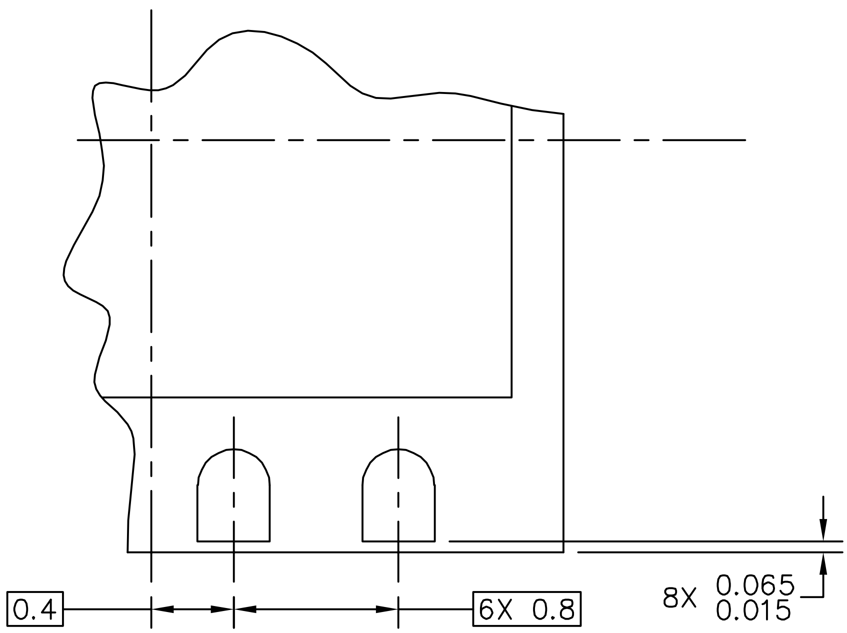
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

5. THE LEAD WIDTH DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION SHALL BE 0.08mm TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46mm.



DETAIL M

BACKSIDE PIN 1 INDEX



DETAIL N

TITLE: THERMALLY ENHANCED DUAL FLAT NO LEAD PACKAGE (DFN) 8 TERMINAL, 0.8 PITCH (4 X 4 X 1)	CASE NUMBER: 1452–01	
	STANDARD: NON–JEDEC	
	PACKAGE CODE: 6165	SHEET: 3 OF 5

MECHANICAL OUTLINES DICTIONARY

DO NOT SCALE THIS DRAWING

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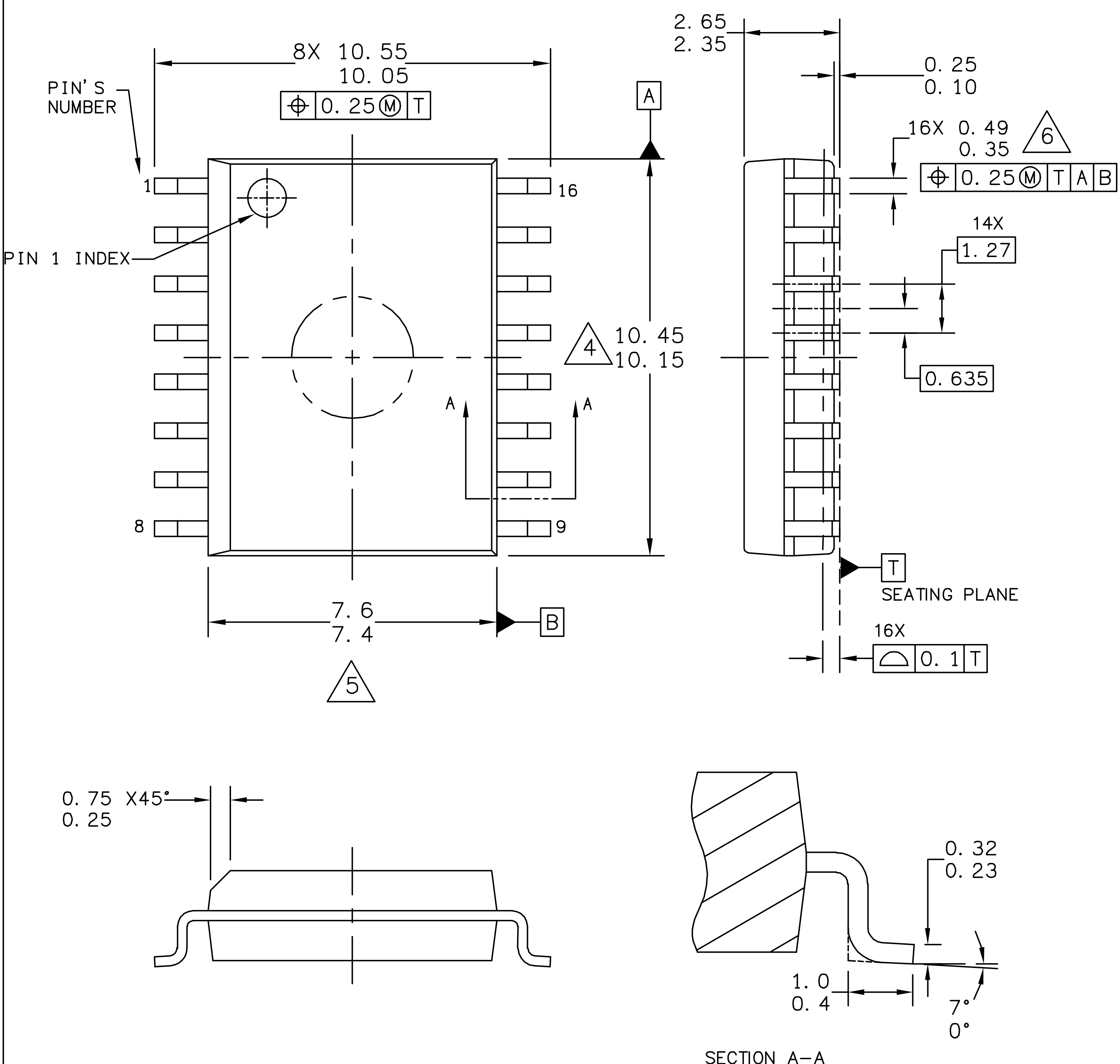

TITLE: 16LD SOIC W/B, 1.27 PITCH CASE-OUTLINE	CASE NUMBER: 751G-05
	STANDARD: JEDEC MS-013AA
	PACKAGE CODE: 2003 — SHEET: 1 OF 3

NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.

2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.

3. DATUMS A AND B TO BE DETERMINED AT THE PLANE WHERE THE BOTTOM OF THE LEADS EXIT THE PLASTIC BODY.

4. THIS DIMENSION DOES NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSION OR GATE BURRS SHALL NOT EXCEED 0.15 MM PER SIDE. THIS DIMENSION IS DETERMINED AT THE PLANE WHERE THE BOTTOM OF THE LEADS EXIT THE PLASTIC BODY.

5. THIS DIMENSION DOES NOT INCLUDE INTER-LEAD FLASH OR PROTRUSIONS. INTER-LEAD FLASH AND PROTRUSIONS SHALL NOT EXCEED 0.25 MM PER SIDE. THIS DIMENSION IS DETERMINED AT THE PLANE WHERE THE BOTTOM OF THE LEADS EXIT THE PLASTIC BODY.

6. THIS DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED 0.62 mm.